



# 100V 3.0mΩ N-Ch Power MOSFET

## Features

- Ultra-low  $R_{DS(ON)}$
- Low Gate Charge
- 100% UIS Tested, 100%  $R_g$  Tested
- Pb-free Lead Plating
- Halogen-free and RoHS-compliant

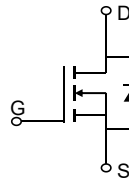
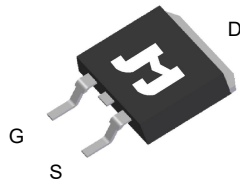
## Product Summary

Parameter	Value	Unit
$V_{DS}$	100	V
$V_{GS(th), Typ}$	3.2	V
$I_D$ (@ $V_{GS} = 10V$ ) <sup>(1)</sup>	184	A
$R_{DS(ON), Typ}$ (@ $V_{GS} = 10V$ )	3	mΩ

## Applications

- Motor Driving in Power Tool, E-vehicle, Robotics
- Current Switching in DC/DC & AC/DC (SR) Sub-systems
- Power Management in Telecom., Industrial Automation, CE

TO-263-3L Top View

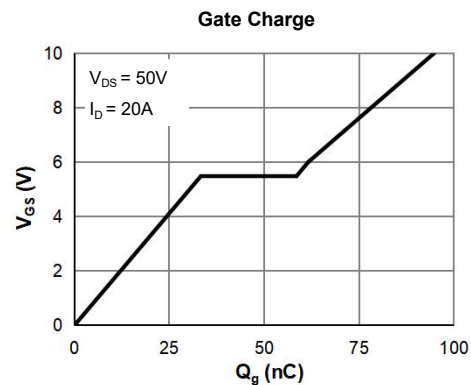
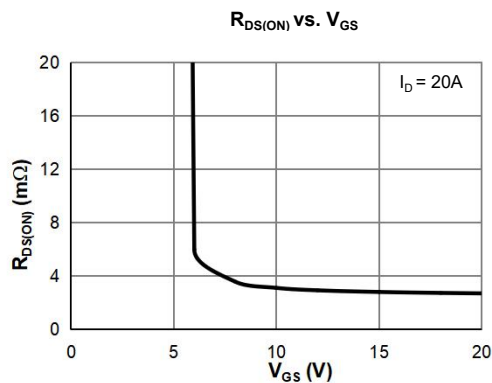


## Ordering Information

Device	Package	# of Pins	Marking	MSL	$T_J$ (°C)	Media	Quantity (pcs)
JVE103T	TO-263-3L	3	VE103T	3	-55 to 150	13-inch Reel	800

**Absolute Maximum Ratings** (@  $T_A = 25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DS}$	100	V
Gate-to-Source Voltage	$V_{GS}$	±20	V
Continuous Drain Current <sup>(1)</sup>	$I_D$	$T_C = 25^\circ\text{C}$	184
		$T_C = 100^\circ\text{C}$	132
Pulsed Drain Current <sup>(2)</sup>	$I_{DM}$	736	A
Avalanche Energy <sup>(3)</sup>	$E_{AS}$	794	mJ
Power Dissipation <sup>(4)</sup>	$P_D$	$T_C = 25^\circ\text{C}$	240
		$T_C = 100^\circ\text{C}$	96
Junction & Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	°C





**Electrical Characteristics** (@  $T_J = 25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
<b>STATIC PARAMETERS</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	100			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 80\text{V}, V_{GS} = 0\text{V}$ $T_J = 55^\circ\text{C}$			1.0 5.0	$\mu\text{A}$
Gate-Body Leakage Current	$I_{GSS}$	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$			$\pm 100$	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	2.0	3.2	4.0	V
Static Drain-Source ON-Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{V}, I_D = 20\text{A}$		3.0	3.9	$\text{m}\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS} = 5\text{V}, I_D = 20\text{A}$		35.9		S
Diode Forward Voltage	$V_{SD}$	$I_S = 1\text{A}, V_{GS} = 0\text{V}$		0.70	1.0	V
Diode Continuous Current	$I_S$	$T_C = 25^\circ\text{C}$			184	A

<b>DYNAMIC PARAMETERS <sup>(5)</sup></b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{V}, V_{DS} = 50\text{V}, f = 1\text{MHz}$		5972		pF
Output Capacitance	$C_{oss}$			1181		pF
Reverse Transfer Capacitance	$C_{rss}$			43		pF
Gate Resistance	$R_g$	$V_{GS} = 0\text{V}, V_{DS} = 0\text{V}, f = 1\text{MHz}$		2.1		$\Omega$

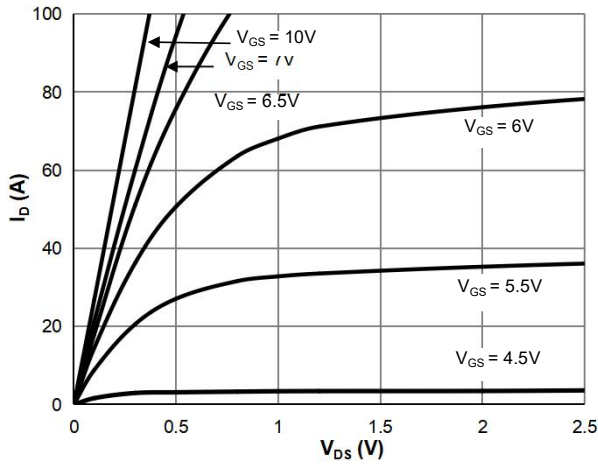
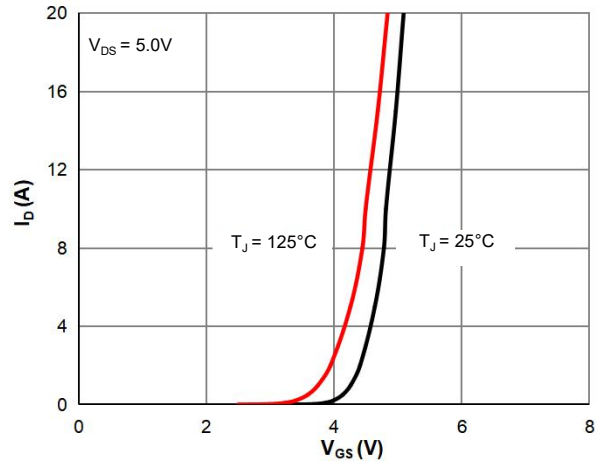
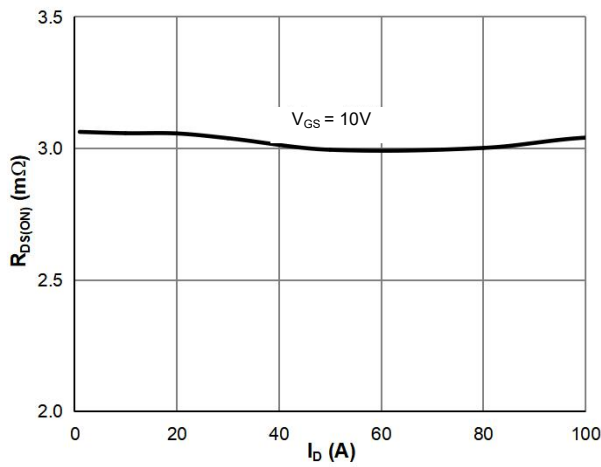
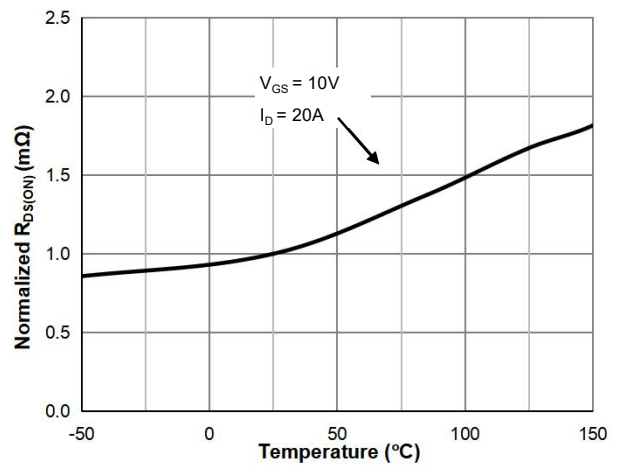
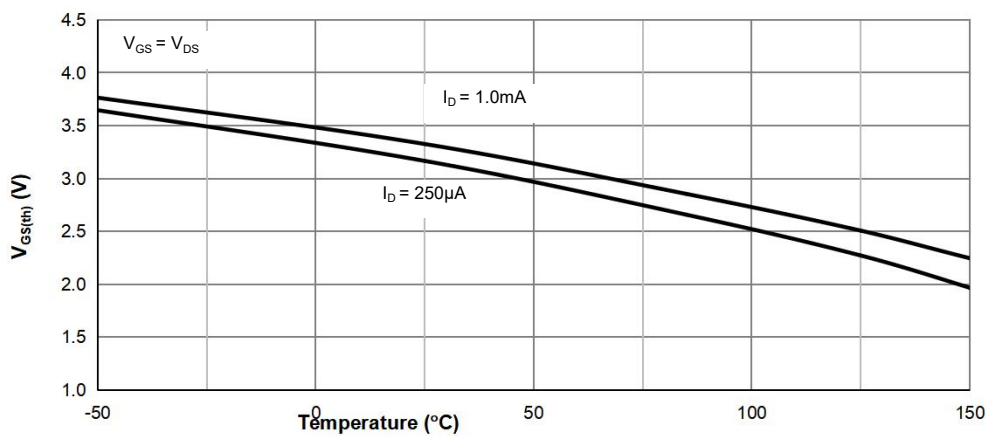
<b>SWITCHING PARAMETERS <sup>(5)</sup></b>						
Total Gate Charge (@ $V_{GS} = 10\text{V}$ )	$Q_g$	$V_{GS} = 0 \text{ to } 10\text{V}$ $V_{DS} = 50\text{V}, I_D = 20\text{A}$		95		nC
Total Gate Charge (@ $V_{GS} = 6\text{V}$ )	$Q_g$			62		nC
Gate Source Charge	$Q_{gs}$			33		nC
Gate Drain Charge	$Q_{gd}$			25		nC
Turn-On DelayTime	$t_{D(on)}$			22		ns
Turn-On Rise Time	$t_r$	$V_{GS} = 10\text{V}, V_{DS} = 50\text{V}$ $R_L = 2.5\Omega, R_{GEN} = 3\Omega$		31		ns
Turn-Off DelayTime	$t_{D(off)}$			48		ns
Turn-Off Fall Time	$t_f$			30		ns
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 15\text{A}, dI_F/dt = 100\text{A}/\mu\text{S}$		74		ns
Body Diode Reverse Recovery Charge	$Q_{rr}$	$I_F = 15\text{A}, dI_F/dt = 100\text{A}/\mu\text{S}$		169		nC

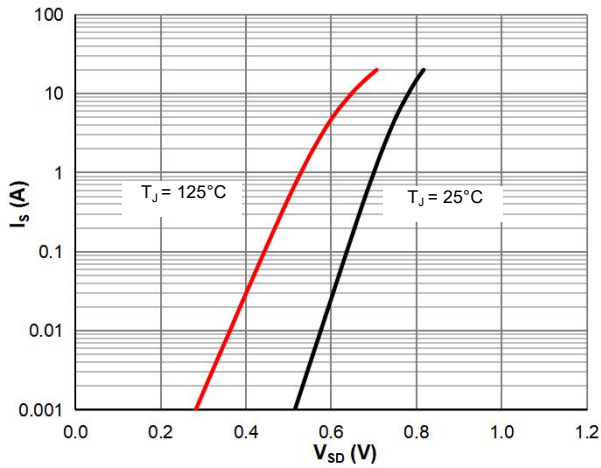
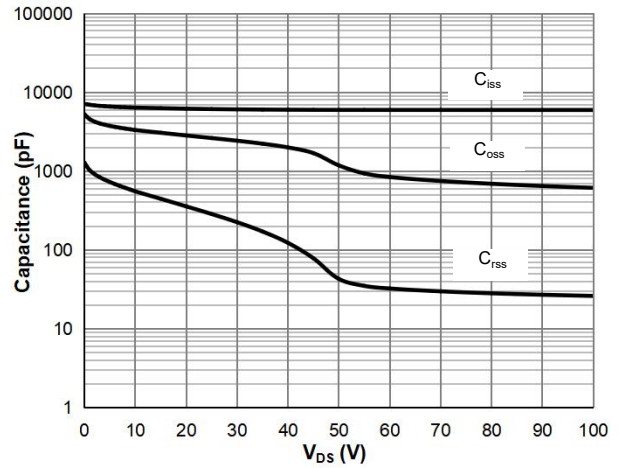
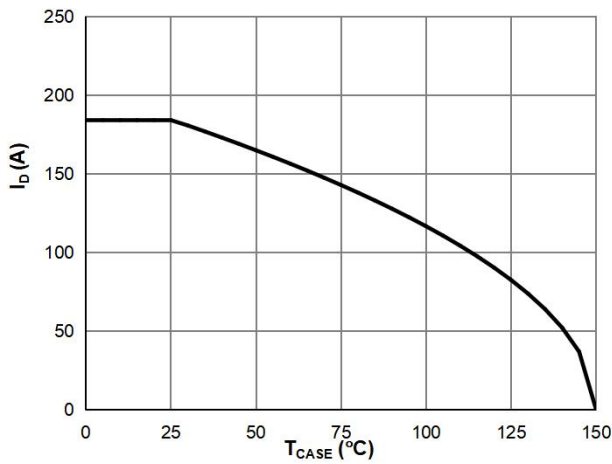
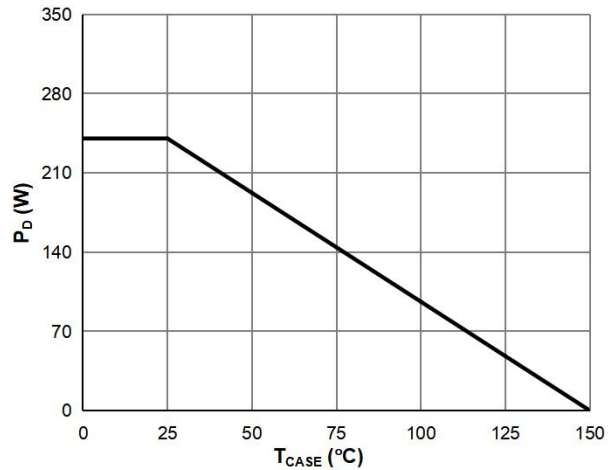
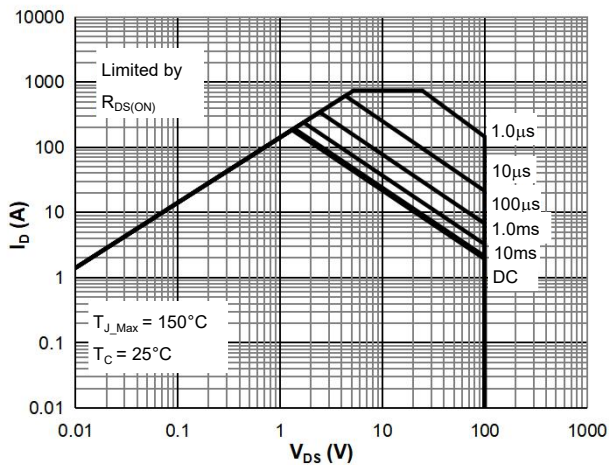
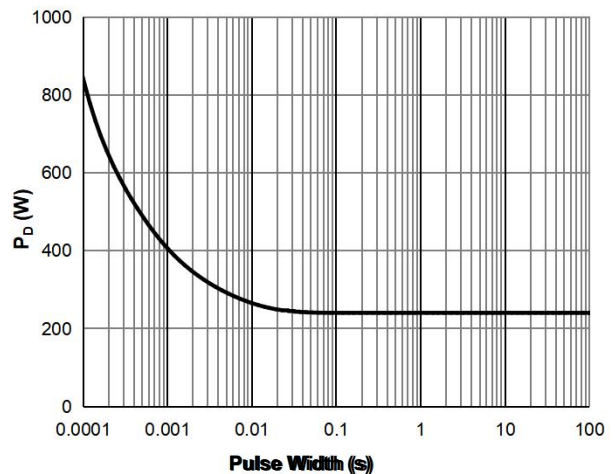
**Thermal Performance**

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	49	57	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.40	0.52	$^\circ\text{C}/\text{W}$

**Notes:**

1. Computed continuous current assumes the condition of  $T_{J\_Max}$  while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. This single-pulse measurement was taken under  $T_{J\_Max} = 150^\circ\text{C}$ .
3.  $E_{AS}$  of 794 mJ is based on starting  $T_J = 25^\circ\text{C}$ ,  $L = 3.0\text{mH}$ ,  $I_{AS} = 23\text{A}$ ,  $V_{GS} = 10\text{V}$ ,  $V_{DD} = 50\text{V}$ ; 100% test at  $L = 0.3\text{mH}$ ,  $I_{AS} = 53.1\text{A}$ .
4. The power dissipation  $P_D$  is based on  $T_{J\_Max} = 150^\circ\text{C}$ .
5. This value is guaranteed by design hence it is not included in the production test.

**Typical Electrical & Thermal Characteristics**

**Figure 1: Saturation Characteristics**

**Figure 2: Transfer Characteristics**

**Figure 3:  $R_{DS(ON)}$  vs. Drain Current**

**Figure 4:  $R_{DS(ON)}$  vs. Junction Temperature**

**Figure 5:  $V_{GS(th)}$  vs. Junction Temperature**

**Typical Electrical & Thermal Characteristics**

**Figure 7: Body-Diode Characteristics**

**Figure 8: Capacitance Characteristics**

**Figure 9: Current De-rating**

**Figure 10: Power De-rating**

**Figure 11: Maximum Safe Operating Area**

**Figure 12: Single Pulse Power Rating, Junction to Case**

Typical Electrical & Thermal Characteristics

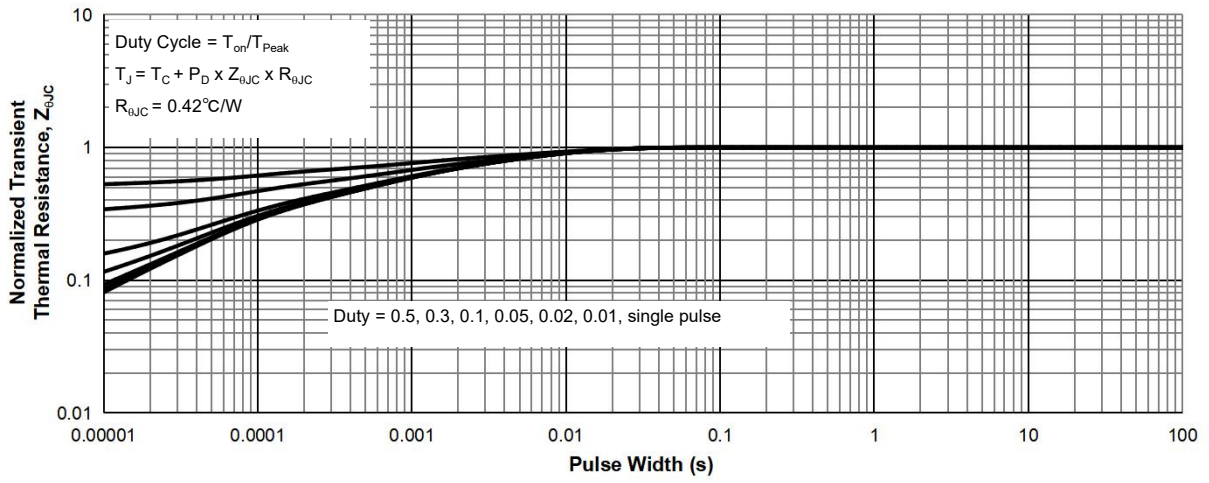
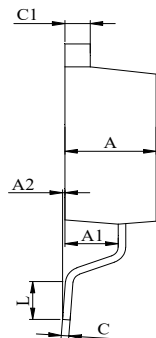
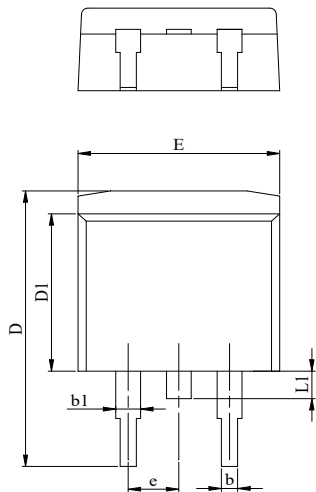
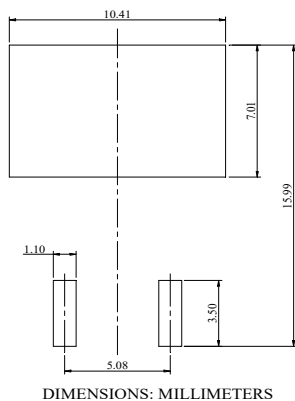


Figure 13: Normalized Maximum Transient Thermal Impedance

**TO-263-3L Package Information**
**Package Outline**


DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	4.24		4.77
A1	2.30		2.89
A2	0.00	0.10	0.25
b	0.70		0.96
b1	1.17		1.70
C	0.30		0.60
C1	1.15		1.42
D	14.10		15.88
D1	8.50		9.60
E	9.78		10.36
L	1.78		2.79
L1			1.75
e		2.54	

**Recommend Soldering Footprint**


DIMENSIONS: MILLIMETERS